CEL

PHOTOCOUPLER
PS2732-1,PS2733-1

HIGH COLLECTOR TO EMITTER VOLTAGE SOP MULTI PHOTOCOUPLER

–NEPOC Series–

DESCRIPTION

The PS2732-1 and PS2733-1 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon darlington-connected phototransistor.

This package is SOP (Small Outline Package) type and has shield effect to cut off ambient light.

It is designed for high density mounting applications.

FEATURES

- High isolation voltage (BV = 2 500 Vr.m.s.)
- High collector to emitter voltage (V_{CEO} = 300 V: PS2732-1)
  (V_{CEO} = 350 V: PS2733-1)
- SOP (Small Outline Package) type
- High current transfer ratio (CTR = 4 000 % TYP.)
- Ordering number of taping product : PS2732-1-F3, F4, PS2733-1-F3, F4
- UL approved: File No. E72422 (S)
- VDE0884 approved (Option)

APPLICATIONS

- Hybrid IC
- Telephone/Telegraph Receiver
- FAX

ORDERING INFORMATION (Solder Contains Lead)

Part Number	Package	Safety Standard Approval
PS2732-1, PS2733-1	4-pin SOP	Standard products • UL approved
PS2732-1-V, PS2733-1-V	4-pin SOP	VDE0884 approved products (Option)

ORDERING INFORMATION (Pb-Free)

Part Number	Package	Safety Standard Approval
PS2732-1-A, PS2733-1-A	4-pin SOP	Standard products • UL approved
PS2732-1-V-A, PS2733-1-V-A	4-pin SOP	VDE0884 approved products (Option)

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(Previous No. P11312EJ3V0DS00)
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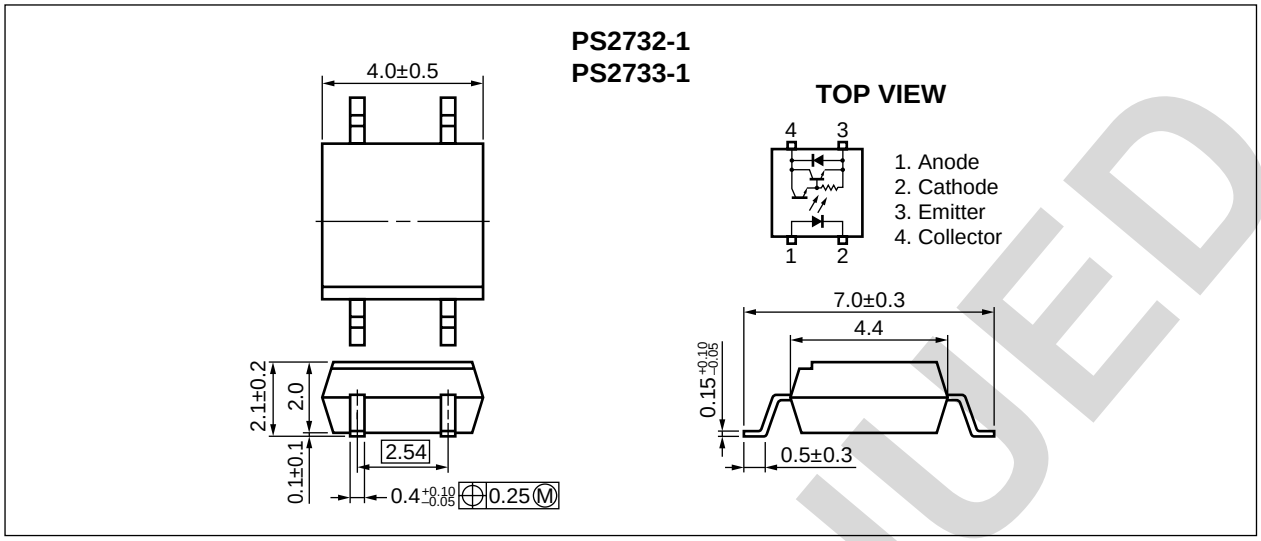
The mark ★ shows major revised points.

★ **PACKAGE DIMENSIONS (in millimeters)**



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings		Unit
			PS2732-1	PS2733-1	
Diode	Forward Current (DC)	I_F	50		mA
	Reverse Voltage	V_R	6		V
	Power Dissipation Derating	ΔP_D/°C	0.8		mW/°C
	Power Dissipation	P_D	80		mW
	Peak Forward Current*1	I_{FP}	1		A
Transistor	Collector to Emitter Voltage	V_{CEO}	300	350	V
	Emitter to Collector Voltage	V_{ECO}	0.3		V
	Collector Current	I_C	150		mA
	Power Dissipation Derating	ΔP_C/°C	1.5		mW/°C
	Power Dissipation	P_C	150		mW
Isolation Voltage*2		BV	2 500		Vr.m.s.
Operating Ambient Temperature		T_A	–55 to +100		°C
Storage Temperature		T_{stg}	–55 to +150		°C

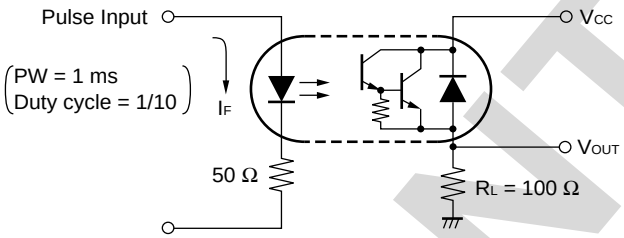
***1** PW = 100 μs, Duty Cycle = 1 %

***2** AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

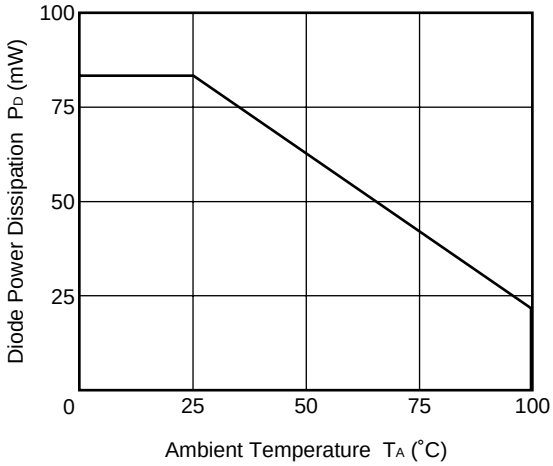
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V_F	I_F = 10 mA		1.15	1.4	V
	Reverse Current	I_R	V_R = 5 V			5	μA
	Terminal Capacitance	C_t	V = 0 V, f = 1 MHz		30		pF
Transistor	Collector to Emitter Dark Current	I_{CEO}	I_F = 0 mA, V_{CE} = 300 V			400	nA
Coupled	Current Transfer Ratio (I_C/I_F)	CTR	I_F = 1 mA, V_{CE} = 2 V	1 500	4 000		%
	Collector Saturation Voltage	$V_{CE (sat)}$	I_F = 1 mA, I_C = 2 mA			1.0	V
	Isolation Resistance	R_{I-O}	V_{I-O} = 1 kV_{DC}	10^{11}			Ω
	Isolation Capacitance	C_{I-O}	V = 0 V, f = 1 MHz		0.4		pF
	Rise Time *1	t_r	V_{CC} = 5 V, I_C = 10 mA, R_L = 100 Ω		100		μs
	Fall Time *1	t_f			100		

***1** Test circuit for switching time

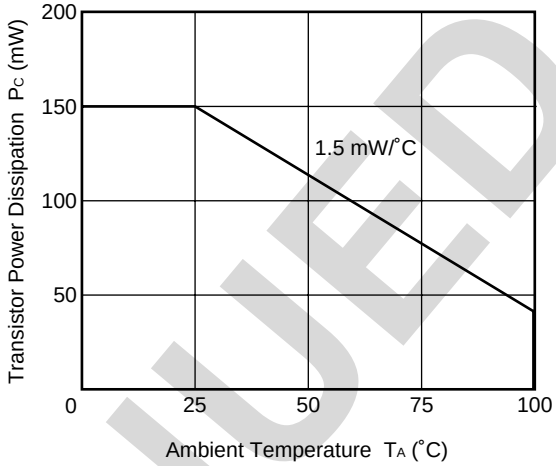


★ TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise specified)

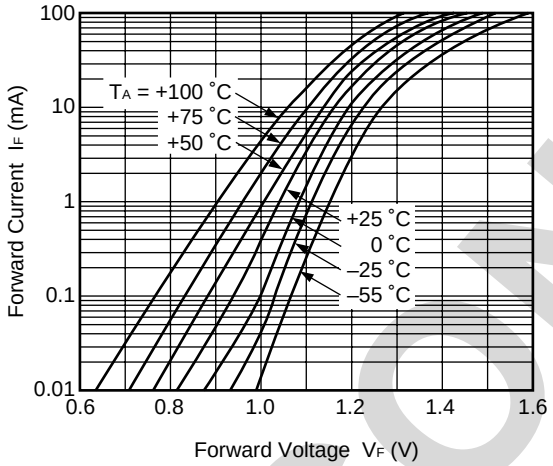
DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



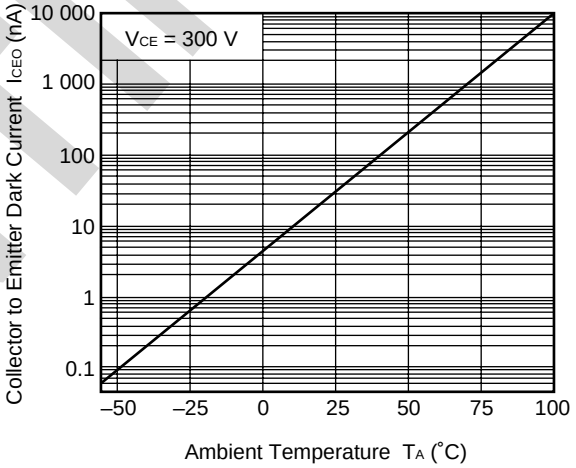
TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



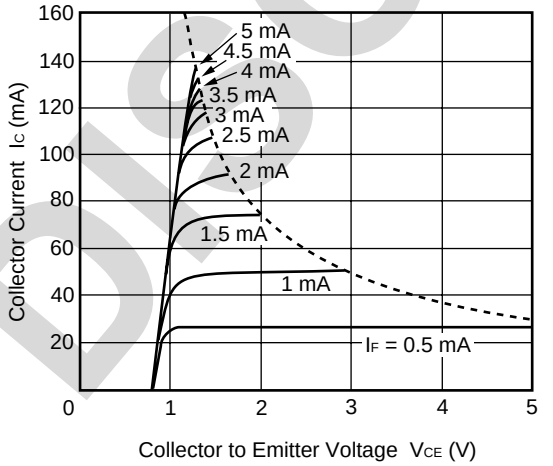
FORWARD CURRENT vs. FORWARD VOLTAGE



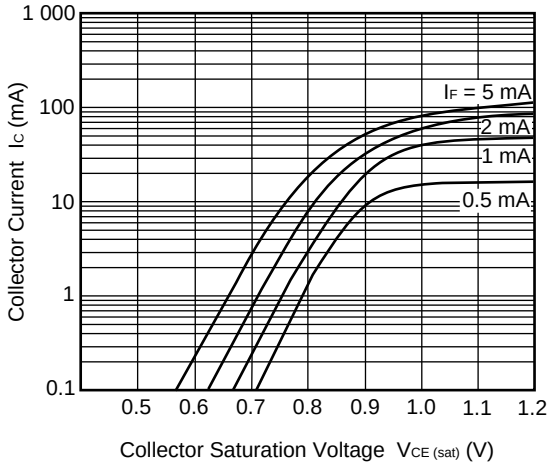
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



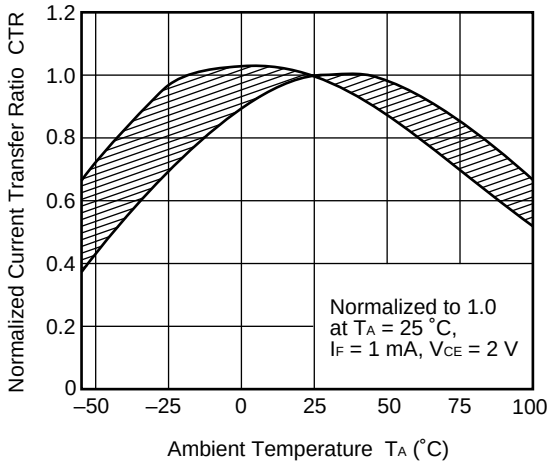
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



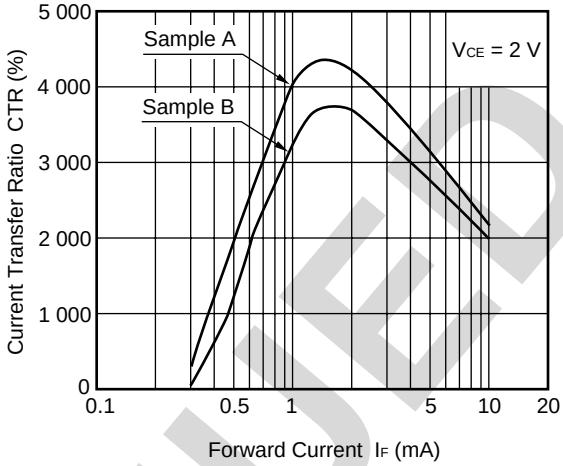
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



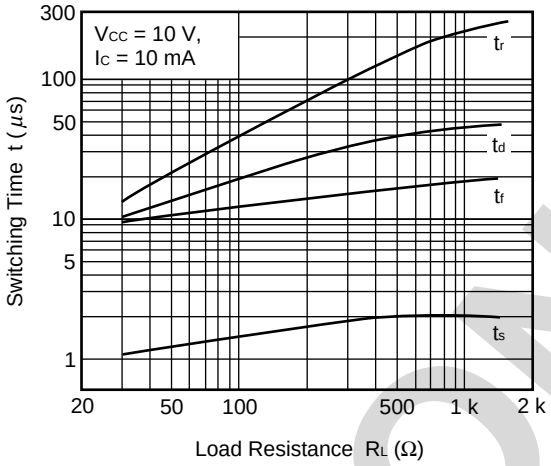
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



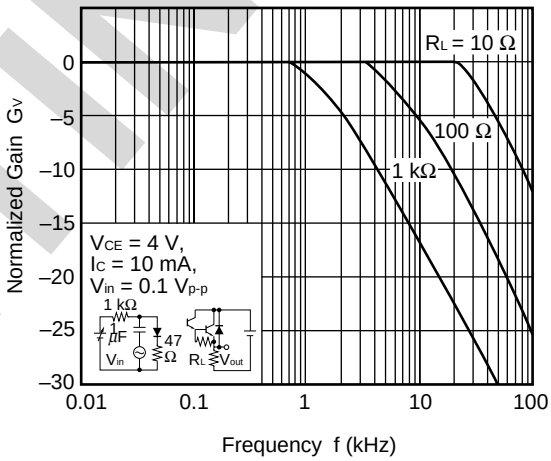
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



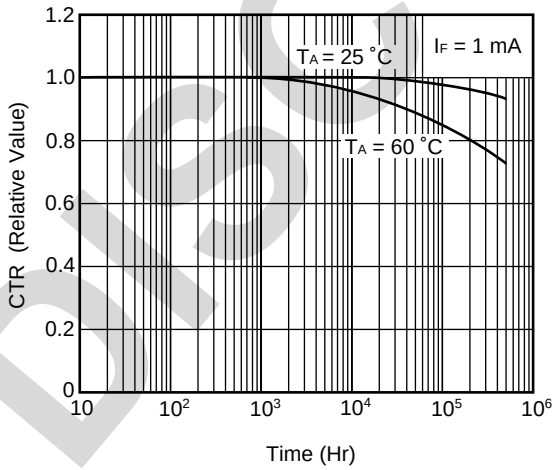
SWITCHING TIME vs. LOAD RESISTANCE



FREQUENCY RESPONSE



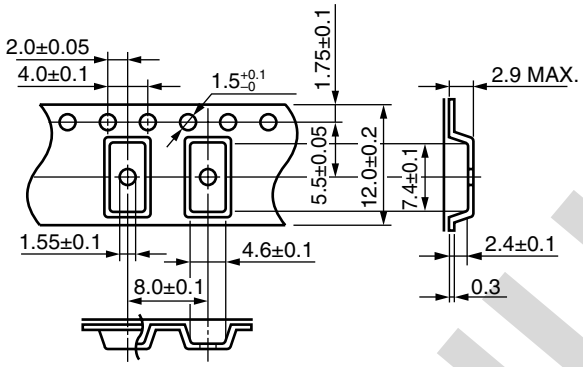
LONG TERM CTR DEGRADATION



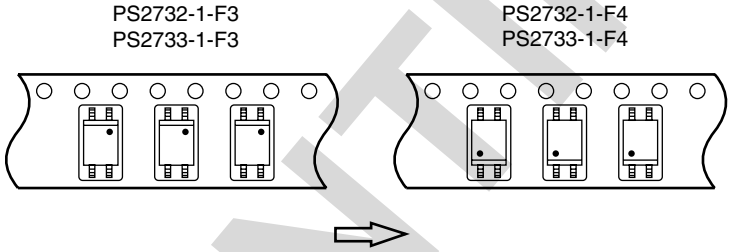
Remark The measurement of TYPICAL CHARACTERISTICS are only for reference, not guaranteed.

★ **TAPING SPECIFICATIONS (in millimeters)**

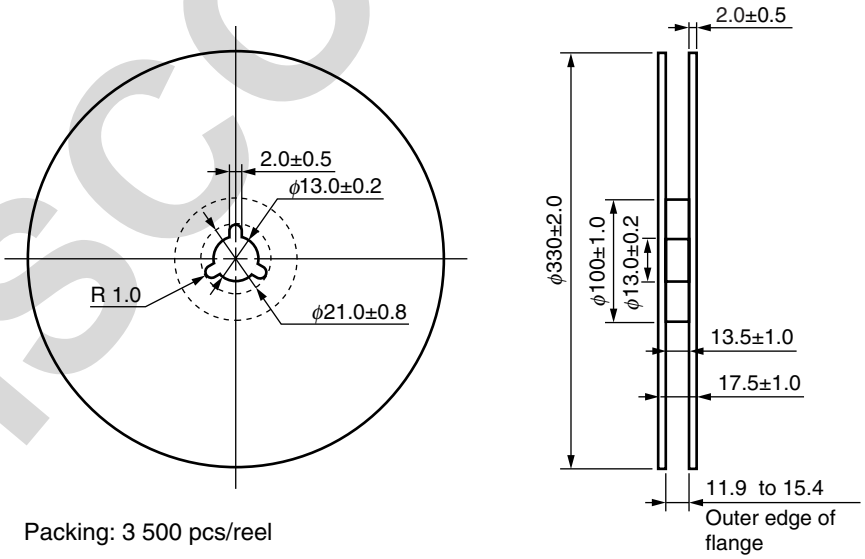
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)



Packing: 3 500 pcs/reel

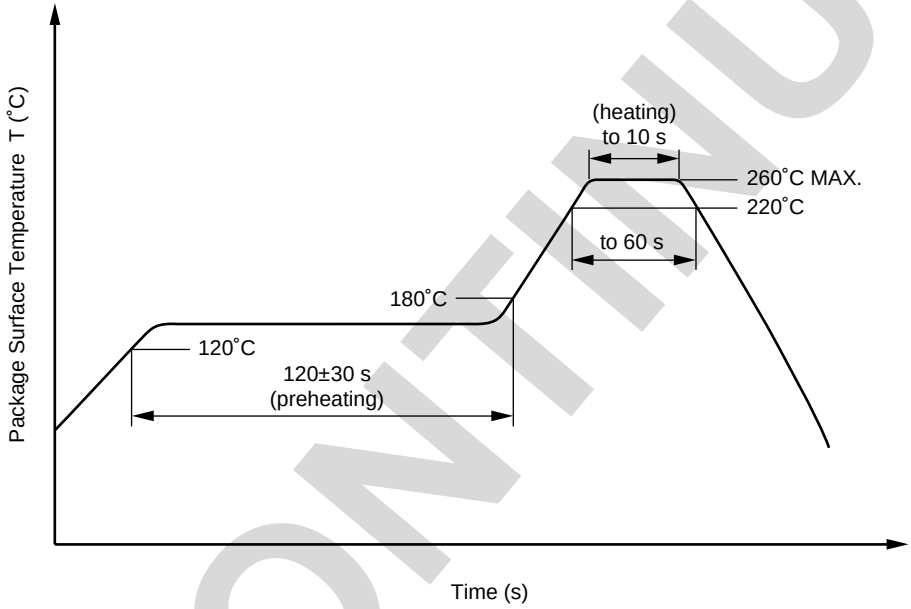
★ NOTES ON HANDLING

1. Recommended soldering conditions

(1) Infrared reflow soldering

• Peak reflow temperature	260°C or below (package surface temperature)
• Time of peak reflow temperature	10 seconds or less
• Time of temperature higher than 220°C	60 seconds or less
• Time to preheat temperature from 120 to 180°C	120±30 s
• Number of reflows	Three
• Flux	Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



(2) Wave soldering

• Temperature	260°C or below (molten solder temperature)
• Time	10 seconds or less
• Preheating conditions	120°C or below (package surface temperature)
• Number of times	One (Allowed to be dipped in solder including plastic mold portion.)
• Flux	Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(3) Cautions

• Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output or between collector-emitters at startup, the output side may enter the on state, even if the voltage is within the absolute maximum ratings.

★ USAGE CAUTIONS

1. Protect against static electricity when handling.
2. Avoid storage at a high temperature and high humidity.

SPECIFICATION OF VDE MARKS LICENSE DOCUMENT (VDE0884)

Parameter	Symbol	Speck	Unit
Application classification (DIN VDE 0109)			
for rated line voltages ≤ 150 Vr.m.s.		IV	
for rated line voltages ≤ 300 Vr.m.s.		III	
Climatic test class (DIN IEC 68 Teil 1/09.80)		55/100/21	
Dielectric strength			
Maximum operating isolation voltage	U_{IORM}	710	V_{peak}
Test voltage (partial discharge test, procedure a for type test and random test)	U_{pr}	850	V_{peak}
$U_{pr} = 1.2 \times U_{IORM}$, $P_d < 5$ pC			
★ Test voltage (partial discharge test, procedure b for all devices test) $U_{pr} = 1.6 \times U_{IORM}$, $P_d < 5$ pC	U_{pr}	1 140	V_{peak}
Highest permissible overvoltage	U_{TR}	4 000	V_{peak}
Degree of pollution (DIN VDE 0109)		2	
Clearance distance		> 5	mm
Creepage distance		> 5	mm
Comparative tracking index (DIN IEC 112/VDE 0303 part 1)	CTI	175	
Material group (DIN VDE 0109)		III a	
Storage temperature range	T_{stg}	–55 to +150	°C
Operating temperature range	T_A	–55 to +100	°C
Isolation resistance, minimum value			
V_{IO} = 500 V dc at T_A = 25 °C	Ris MIN.	10^{12}	Ω
V_{IO} = 500 V dc at T_A MAX. at least 100 °C	Ris MIN.	10^{11}	Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve)			
Package temperature	Tsi	150	°C
Current (input current I_F, Psi = 0)	Isi	300	mA
Power (output or total power dissipation)	Psi	500	mW
Isolation resistance			
V_{IO} = 500 V dc at T_A = 175 °C (Tsi)	Ris MIN.	10^9	Ω

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Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
Lead (Pb)	< 1000 PPM	-A	-AZ
		Not Detected	(*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
PBB	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.